



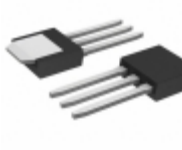




	<h2 style="color: red;">GP1M016A060F</h2>	
	Hersteller-Teilenummer:	GP1M016A060F
	Hersteller / Marke:	Global Power Technologies Group
	Teil der Beschreibung:	MOSFET N-CH 600V 16A TO220F
Datenblätter:	 GP1M016A060F.pdf	
RoHs Status:	Bleifrei / RoHS-konform	
Lagerzustand:	New original, 1991 pcs Stock Available.	
Liefern von:	Hong Kong	
Versandweg:	DHL/Fedex/TNT/UPS/EMS	
<p>Image may be representation. See specs for product details.</p>		

Spezifikationen

Teilenummer	GP1M016A060F
Hersteller	Global Power Technologies Group
Beschreibung	MOSFET N-CH 600V 16A TO220F
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	1991 pcs Stock
Serie	-
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Through Hole
Verpackung / Gehäuse	TO-220-3 Full Pack
Supplier Device-Gehäuse	TO-220F
Verlustleistung (max)	48W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	600V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	16A (Tc)
Rds On (Max) @ Id, Vgs	470 mOhm @ 8A, 10V
VGS (th) (Max) @ Id	4V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	53nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	3039pF @ 25V
Verpackung	Tube

GP1M016A060F ist neu im Original. Suche GP1M016A060F Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie GP1M016A060F Global Power Technologies Group mit Garantie und Vertrauen. Anfrage GP1M016A060F: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>GP1M015A050H Global Power Technologies Group MOSFET N-CH 500V 14A TO220</p>	 <p>GP1M016A025HG Global Power Technologies Group MOSFET N-CH 250V 16A TO220</p>	 <p>GP1M018A020CG Global Power Technologies Group MOSFET N-CH 200V 18A DPAK</p>	 <p>GP1M016A025PG Global Power Technologies Group MOSFET N-CH 250V 16A IPAK</p>
 <p>GP1M016A060H Global Power Technologies Group MOSFET N-CH 600V 16A TO220</p>	 <p>GP1M016A025FG Global Power Technologies Group MOSFET N-CH 250V 16A TO220F</p>	 <p>GP1M018A020FG Global Power Technologies Group MOSFET N-CH 200V 18A TO220F</p>	 <p>GP1M016A060FH Global Power Technologies Group MOSFET N-CH 600V 16A TO220F</p>

heiße Teile

Mehr

⊗ GP1FA553RZOF	↔ GP1FA553TZ0F	⇒ GP1FAV31TK0F	D GP1FAV50RK0F	↔ GP1FAV50TK0F
⊣ GP1FAV51TK0F	⊗ GP1FD320TP0F	D GP1FM313TMF5	⇒ GP1FM313TZMF	↔ GP1FSV51TK0F
⊗ GP1L53VJ000F	⊣ GP1L57J0000F	⊗ GP1M003A050FG	↔ GP1M003A080CH	↔ GP1M003A090C
D GP1M006A070FH	⊗ GP1M007A090H	⊣ GP1M008A025PG	⊗ GP1M009A020FG	↔ GP1M009A090N
⇒ GP1M010A060H	↔ GP1M010A080FH	⊗ GP1M011A050FH	⊣ GP1M013A050H	↔ GP1M016A025CG
↔ GP1M016A060H	⇒ GP1S092HCPI	D GP1S092HCPIF	⊗ GP1S092HCPIF	⊣ GP1S092HCPKF
⊗ GP1S093HCZ	D GP1S093HCZ0F	⇒ GP1S093HCZ0F	↔ GP1S093HCZ0F	↔ GP1S094HCZ0F
⊣ GP1S094HCZ0F	⊗ GP1S094HCZ0F	↔ GP1S096HCZ	⇒ GP1S096HCZ0F	↔ GP1S096HCZ0F
⊗ GP1S097HCZ0F	⊣ GP1S194HCZ0F	⊗ GP1S194HCZ0F	D GP1S195HCPS4	↔ GP1S195HCPSF
↔ GP1S196HCCSF	⊗ GP1S196HCPSF	⊣ GP1S196HCPSF	⊗ GP1S196HCPSF4	↔ GP1S196HCZ0F

Contact us: Info@Y-IC.com

HINZUFÜGEN: Einheit A5-B5 Nr.509, 5 / F Sing Win Fabrikgebäude, 15-17 Shing Yip St, Kwun Tong, Kowloon, HongKong.

Copyright © 2019 YIC International Co., Limited